Integrated Device Technology, Inc. 2975 Stender Way, Santa Clara, CA - 95054 PRODUCT/PROCESS CHANGE NOTICE (PCN)					
PCN #: L0108-01R1 Product Affected: IDTQS3V IDTQS3V		MEANS OF DIST Product Mark Back Mark Date Code 	INGUISHING CHA	,	
Date Effective: November 1	3, 2001	□ Other			
Contact: Bimla Paul					
Title: Q. A. Manager		Attachment::	Yes	🗌 No	
Phone #: (408) 654-6419					
Fax #: (408) 492-8362		Samples: Ava	ailable upon request		
E-mail: bimla.paul@idt.c	om	1	1 1		
 DESCRIPTION AND PURPO Die Technology Wafer Fabrication Process Assembly Process Equipment Material Testing Manufacturing Site Data Sheet Other 	SE OF CHANGE: PCN addendum to correct PC should be replaced with "YQ YQ: IDTQS3VH125, IDTQS ZQ: IDTQS3VH257, IDTQS The PCN effectivity date is N	" or " ZQ " as follow 53VH126 53VH2245, IDTQS:	: 32XVH2245, IDTQS	34XVH2245	
RELIABILITY/QUALIFICA There will be no impact or effe	TION SUMMARY: ct on the product reliability. The q	ualification data is a	ttached.		
to grant approval or request add it will be assumed that this char	equire written notification of this c litional information. If IDT does n nge is acceptable. ither version manufactured after th	ot receive acknowle	dgement within 30 d	ays of this notice	
Customer:		Approval fo	r shipments prior	• to effective date.	
Name/Date:	E-1	Mail Address:			
Title:	Ph	one# /Fax# :			
CUSTOMER COMMENTS:					
IDT ACKNOWLEDGMENT	OF RECEIPT:				
		DATE:			
IDT FRA-1509-01 REV. 00	09/18/01 PAGE	1 OF 1		REFER TO QCA-1795	

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PRODUCT/PROCESS CHANGE NOTICE (PCN) ATTACHMENT - PCN #: L0108-01R1 (Addendum)

PCN Type:	Die revision

No

Data Sheet Change

Detail of Change

The die has been revised from "YQ" , "ZQ" and "QC" stepping to "Z" stepping

Die Revision Details

	<u>Current Die Rev</u> YQ	<u>Current Die Rev</u> ZQ	<u>Current Die Rev</u> QC	<u>New Die Rev</u> Z
Wafer Fab Technology	0.8µm	0.8μm	0.8µm	0.8µm
Poly Gate	0.8µm	0.8µm	0.8µm	0.8µm
Minimum Gate Oxide	150Å	150Å	150Å	150Å
Thickness				
Wafer Size	6"	6"	6"	6"
Fab Facility	Fab 5	Fab 5	Fab 2	Fab 2
	(PSA, Australia)	(PSA, Australia)	(Salinas, CA)	(Salinas, CA)
Date Code Prefix	YQ	ZQ	QC	Z
Affected Parts	IDTQS3VH125	IDTQS3VH257	IDTQS3VH125	IDTQS3VH125
	IDTQS3VH126	IDTQS3VH2245	IDTQS3VH126	IDTQS3VH126
		IDTQS32XH2245	IDTQS3VH257	IDTQS3VH257
		IDTQS34XVH2245	IDTQS3VH2245	IDTQS3VH2245
			IDTQS32XVH2245	IDTQS32XVH2245
			IDTQS34XVH2245	IDTQS34XVH2245

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PRODUCT/PROCESS CHANGE NOTICE (PCN) ATTACHMENT - PCN #: L0108-01R1 (Addendum)

Qualification Plan QLG-01-01

Test Vehicle: IDTQS3VH862

Qualification Test Plan and Results:

Test Description	SS/Acc #	Test Results
Dynamic High Temp Operating Life Test Mil-Std-883, Method-1005	116/0	116/0
ESD - HBM Mil-Std-883, Method-3015	3/0	3500 Volts
ESD-CDM JESD22-C101	3/0	1000 Volts
ESD-MM EIAJ-IC-121	3/0	400 Volts
Latch-up EIA/JESD78	10/0	10/0

Characterization Data:

Characterization data is available upon request.